

Search History. 35 pp. ~~45~~ (05/14/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	(light adj extraction near5 light-emitting adj diode).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 20:33
L2	2	"20040070004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 20:40
L3	0	tran.xp. and minhloan.in. and 257/10\$.ccs.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 20:41
L4	31	tran.xp. and minhloan.xp. and 257/10\$.ccs.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 20:41
S1	23	("r.sub.max" roughness) and (otft thin adj film adj transistor tft) and (rms root-mean-square) and (si silicon) near12 (germanium ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/16 14:43
S2	19	("r.sub.max" roughness) and (otft thin adj film adj transistor tft) and (rms root-mean-square) and (si silicon) near12 (germanium ge) and (iron fe ni nickel co cobalt ru ruthenium pd palladium os osmium ir iridium pt platinum cu copper au gold)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 18:31
S3	23	("r.sub.max" roughness) and (otft thin adj film adj transistor tft) and (rms root-mean-square) and (si silicon) near8 (germanium ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 18:33
S4	132	("r.sub.max" roughness) and (otft thin adj film adj transistor tft) and (si silicon) near8 (germanium ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 18:33
S5	114	("r.sub.max" roughness) and (thin adj film adj transistor tft) and (si silicon) near8 (germanium ge) and nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 18:34

S6	91	((("r.sub.max" roughness) and (thin adj film adj transistor tft) and (si silicon) near8 (germanium ge) and nm) not (("r.sub.max" roughness) and (otft thin adj film adj transistor tft) and (rms root-mean-square) and (si silicon) near8 (germanium ge)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 18:34
S7	23	(US-6521492-\$ or US-6246070-\$ or US-5707744-\$ or US-5893949-\$ or US-6569748-\$ or US-6468923-\$ or US-6107639-\$ or US-6221738-\$ or US-6521909-\$).did. or (US-20020182785-\$ or US-20030062546-\$ or US-20030062522-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20010003659-\$ or US-20020119585-\$ or US-20030089909-\$ or US-20030049892-\$ or US-20030054593-\$ or US-20010046729-\$ or US-20030042486-\$ or US-20020187594-\$ or US-20020013114-\$).did.	US-PGPUB; USPAT	OR	OFF	2003/10/08 12:28
S8	15	((("5693541") or ("5932393") or ("6048758") or ("6160279") or ("6331457") or ("6444390") or ("6475840") or ("6479333") or ("6432684") or ("6489189") or ("20010034088") or ("20020008286") or ("20020014625") or ("20020038889") or ("20020043662")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/10/08 12:28
S9	1	("5693541").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/10/08 12:23
S10	1	("5932893").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/10/08 12:24
S11	1	("6482684").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/10/08 12:25
S12	0	jp-2001035787.\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 12:26

S13	2	jp-2001035787\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 12:26
S14	2	jp-2001060551\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 12:27
S15	2	jp-08078329\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 12:27
S16	23	((("5693541") or ("5932393") or ("6048758") or ("6160279") or ("6331457") or ("6444390") or ("6475840") or ("6479333") or ("6432684") or ("6489189") or ("20010034088") or ("20020008286") or ("20020014625") or ("20020038889") or ("20020043662")).PN.) or (("5693541").PN.) or (("5932893").PN.) or (("6482684").PN.) or jp-2001035787\$-\$\$.did. or jp-2001060551\$-\$\$.did. or jp-08078329\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 12:30
S17	22	(US-6444390-\$ or US-6475840-\$ or US-6482684-\$ or US-6489189-\$ or US-6479333-\$ or US-5693541-\$ or US-6331457-\$ or US-6160279-\$ or US-6048758-\$ or US-5932893-\$ or US-6432684-\$).did. or (US-20020043662-\$ or US-20020008286-\$ or US-20010034088-\$ or US-20020038889-\$ or US-20020014625-\$).did. or (JP-08078329-\$ or JP-2001035787-\$ or JP-2001060551-\$).did. or (JP-08078329-\$ or JP-2001060551-\$ or JP-2001035787-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/08 12:31
S18	3	"187414".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 14:45

S19	412	(thin adj film adj transistor tft otft).ti,ab,clm. and (roughness p-v rms root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 14:47
S20	290	(thin adj film adj transistor tft otft).ti,ab,clm. and surface near12 (roughness p-v rms root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 14:48
S21	56	(thin adj film adj transistor tft otft).ti,ab,clm. and surface near12 (roughness p-v rms root-mean-square) near12 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 16:41
S22	0	"yamaguchi.in" near2 shinya.in. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 16:33
S23	0	"yamaguchi.in" near2 shinya.in. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 16:33
S24	29	yamaguchi.in. near2 shinya.in. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 16:33

S25	49	(US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 16:32
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S26	2	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface near15 surface adj roughness near15 (rms root-mean-square) near15 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 16:43
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S27	4	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface adj roughness near15 (rms root-mean-square) near15 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 17:07
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S28	4	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface adj roughness near15 (rms root-mean-square) near15 nm and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 17:11
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S29	5	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface adj roughness near15 (rms root-mean-square p-v peak-to-valley) near15 nm and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 17:12
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S30	2	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface adj roughness near15 (p-v peak-to-valley peak adj "to" adj valley) near15 nm and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 08:21
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S31	2	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface near3 roughness near15 (p-v peak-to-valley peak adj "to" adj valley) near15 nm and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 08:22
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S32	2	((US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020164842-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.) and surface near6 roughness near15 (p-v peak-to-valley peak adj "to" adj valley) near15 nm and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 08:22
S33	5	surface near6 roughness near15 (p-v peak-to-valley peak adj "to" adj valley) near15 nm and germanium and (tft thin adj film adj transistor otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 08:22

S34	22	(US-5932893-\$ or US-6048758-\$ or US-6331457-\$ or US-6160279-\$ or US-6489189-\$ or US-6482684-\$ or US-6432684-\$ or US-6444390-\$ or US-6475840-\$ or US-6479333-\$ or US-5693541-\$).did. or (US-20020014625-\$ or US-20020043662-\$ or US-20020038889-\$ or US-20020008286-\$ or US-20010034088-\$).did. or (JP-2001060551-\$ or JP-08078329-\$ or JP-2001035787-\$).did. or (JP-2001060551-\$ or JP-2001035787-\$ or JP-08078329-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 15:27
S35	3362	((257/49) or (257/59) or (257/63) or (257/66) or (257/70) or (257/72) or (257/75)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:20
S36	1995	((((257/49) or (257/59) or (257/63) or (257/66) or (257/70) or (257/72) or (257/75)).CCLS.) AND THIN ADJ FILM ADJ TRANSISTOR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 15:31
S37	1769	((((257/49) or (257/59) or (257/63) or (257/66) or (257/70) or (257/72) or (257/75)).CCLS.) AND (THIN ADJ FILM ADJ TRANSISTOR tft otft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 15:31
S38	37	((((257/49) or (257/59) or (257/63) or (257/66) or (257/70) or (257/72) or (257/75)).CCLS.) AND (THIN ADJ FILM ADJ TRANSISTOR tft otft).ti,ab,clm. and roughness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 15:32

S39	113	(US-6048758-\$ or US-6160279-\$ or US-5693541-\$ or US-6432684-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-5266824-\$ or US-6246070-\$ or US-6515299-\$ or US-5943560-\$ or US-5981974-\$ or US-6521909-\$ or US-6521492-\$ or US-6569748-\$ or US-6468923-\$ or US-5893949-\$ or US-6221738-\$ or US-6107639-\$ or US-6444390-\$ or US-6475840-\$ or US-6479333-\$ or US-6489189-\$ or US-6331457-\$ or US-6482684-\$).did. or (US-6180957-\$ or US-6225966-\$ or US-6281057-\$ or US-6326249-\$ or US-6358765-\$ or US-6608326-\$ or US-6097453-\$ or US-6163055-\$ or US-6597014-\$ or US-6534353-\$ or US-5707744-\$ or US-5932893-\$ or US-6437366-\$ or US-6396105-\$ or US-6441873-\$ or US-6521913-\$ or US-6124602-\$ or US-6115094-\$ or US-6115090-\$ or US-6093937-\$ or US-6011275-\$ or US-5757030-\$ or US-5693959-\$ or US-5668379-\$ or US-5621224-\$ or US-6437368-\$ or US-6331717-\$).did. or (US-6310667-\$ or US-6271543-\$ or US-6501095-\$ or US-4960719-\$ or US-4597160-\$ or US-5243202-\$ or US-5221365-\$).did. or (US-20020043662-\$ or US-20030122125-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20010034088-\$ or US-20030042486-\$ or US-20020187594-\$ or US-20020182785-\$ or US-20030062546-\$ or US-20030062522-\$ or US-20030054593-\$ or US-20010046729-\$ or US-20020013114-\$ or US-20010003659-\$ or US-20030049892-\$ or US-20020014625-\$ or US-20020038889-\$ or US-20020008286-\$ or US-20030025118-\$ or US-20030059986-\$ or US-20030064571-\$ or US-20030094658-\$ or US-20030160239-\$ or US-20010000755-\$ or US-20020066931-\$ or US-20020102823-\$).did. or (US-20020113241-\$ or US-20020113248-\$ or	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 15:35
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S40	8	((US-6048758-\$ or US-6160279-\$ or US-5693541-\$ or US-6432684-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-5266824-\$ or US-6246070-\$ or US-6515299-\$ or US-5943560-\$ or US-5981974-\$ or US-6521909-\$ or US-6521492-\$ or US-6569748-\$ or US-6468923-\$ or US-5893949-\$ or US-6221738-\$ or US-6107639-\$ or US-6444390-\$ or US-6475840-\$ or US-6479333-\$ or US-6489189-\$ or US-6331457-\$ or US-6482684-\$).did. or (US-6180957-\$ or US-6225966-\$ or US-6281057-\$ or US-6326249-\$ or US-6358765-\$ or US-6608326-\$ or US-6097453-\$ or US-6163055-\$ or US-6597014-\$ or US-6534353-\$ or US-5707744-\$ or US-5932893-\$ or US-6437366-\$ or US-6396105-\$ or US-6441873-\$ or US-6521913-\$ or US-6124602-\$ or US-6115094-\$ or US-6115090-\$ or US-6093937-\$ or US-6011275-\$ or US-5757030-\$ or US-5693959-\$ or US-5668379-\$ or US-5621224-\$ or US-6437368-\$ or US-6331717-\$).did. or (US-6310667-\$ or US-6271543-\$ or US-6501095-\$ or US-4960719-\$ or US-4597160-\$ or US-5243202-\$ or US-5221365-\$).did. or (US-20020043662-\$ or US-20030122125-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20010034088-\$ or US-20030042486-\$ or US-20020187594-\$ or US-20020182785-\$ or US-20030062546-\$ or US-20030062522-\$ or US-20030054593-\$ or US-20010046729-\$ or US-20020013114-\$ or US-20010003659-\$ or US-20030049892-\$ or US-20020014625-\$ or US-20020038889-\$ or US-20020008286-\$ or US-20030025118-\$ or US-20030059986-\$ or US-20030064571-\$ or US-20030094658-\$ or US-20030160239-\$ or US-20010000755-\$ or US-20020066931-\$ or US-20020102823-\$).did. or (US-20020113241-\$ or US-20020113242-\$ or	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 16:28
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S41	1008	surface adj roughness near4 defined	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 15:40
S42	0	surface adj roughness near4 defined and "R.sub.max."	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 15:40
S43	671	surface adj roughness near4 defined and film	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 15:40
S44	145	surface adj roughness near4 defined ti,ab,clm. and film	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 15:41
S45	3	((("5923962") or ("5643826")).PN. or (2002/0043660).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 16:35

S46	90	(US-6097453-\$ or US-5981974-\$ or US-5943560-\$ or US-5849612-\$ or US-5828080-\$ or US-5714407-\$ or US-5712496-\$ or US-6326249-\$ or US-6281057-\$ or US-5266824-\$ or US-6358765-\$ or US-6180957-\$ or US-6163055-\$ or US-6225966-\$ or US-6608326-\$ or US-6521909-\$).did. or (US-20030160239-\$ or US-20030094658-\$ or US-20030089909-\$ or US-20030064571-\$ or US-20030062546-\$ or US-20030059986-\$ or US-20030054593-\$ or US-20030049892-\$ or US-20030038321-\$ or US-20030032221-\$ or US-20030025118-\$ or US-20020182785-\$ or US-20020043660-\$ or US-20020142567-\$ or US-20020113248-\$ or US-20020113241-\$ or US-20020102823-\$ or US-20020066931-\$ or US-20010003659-\$ or US-20010000755-\$).did. or (JP-2000277742-\$ or JP-2000260992-\$ or JP-2000124463-\$ or JP-2002244138-\$ or JP-2001308341-\$).did. or (JP-2003218029-\$ or JP-2003197636-\$ or US-20030032221-\$ or JP-2001274404-\$ or JP-2000277742-\$ or JP-11231323-\$ or EP-811868-\$ or EP-766119-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2003/10/09 16:32
S47	4	"107592".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/09 16:35
S48	2	("6107639").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 11:40

S49	55	(surface adj roughness "R.sub. max" "Rms") near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9. ccls. "438"/\$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 11:45
S50	54	(surface adj roughness "R.sub. max" "Rms") near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9. ccls. "438"/\$9.ccls.) and roughness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 11:46
S51	21	(surface adj roughness "R.sub. max" "Rms") near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9. ccls. "438"/\$9.ccls.) and roughness and (roughness near3 "nm")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:19
S52	1	(surface adj roughness "R.sub. max" "Rms") near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9. ccls. "438"/\$9.ccls.) and roughness and (roughness near3 "nm") and ("P-V" peak adj2 valley)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:21
S53	1	(sige silicon near1 germanium) near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9.ccls. "438"/\$9.ccls.) and roughness and (roughness near3 "nm") and (("P-V" peak adj2 valley) near4 "nm")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:22
S54	5	(sige silicon near1 germanium) near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9.ccls. "438"/\$9.ccls.) and (("P-V" peak adj2 valley) near4 "nm")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:25
S55	5	(sige silicon near1 germanium) near4 (active adj (region layer film) semiconductor adj (film layer)) and ("257"/\$9.ccls. "438"/\$9.ccls.) and (("P-V" peak adj2 valley peak-to-valley) near4 "nm")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:26
S56	8	(sige silicon near1 germanium) near4 (active adj (region layer film) semiconductor adj (film layer)) and (("P-V" peak adj2 valley peak-to-valley) near4 "nm")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:26

S57	6	(sige silicon near1 germanium) near4 (active adj (region layer film) semiconductor adj (film layer)) and (("P-V" peak adj2 valley peak-to-valley) near4 "nm") and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/22 13:26
S58	22	(US-6479333-\$ or US-6489189-\$ or US-6475840-\$ or US-6444390-\$ or US-6432684-\$ or US-6331457-\$ or US-6160279-\$ or US-5932893-\$ or US-6048758-\$ or US-5693541-\$ or US-6482684-\$).did. or (US-20020014625-\$ or US-20010034088-\$ or US-20020008286-\$ or US-20020043662-\$ or US-20020038889-\$).did. or (JP-2001035787-\$ or JP-2001060551-\$ or JP-08078329-\$).did. or (JP-2001035787-\$ or JP-08078329-\$ or JP-2001060551-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/08/06 17:43
S59	3	"352362".ap.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/08/06 18:00
S60	2	"20020043660"	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/08/06 18:00
S61	5	((("20020043660") or ("5923962") or ("5643826"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 18:03
S62	1	jp-07130652\$-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 18:04
S63	2	jp-08078329\$-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 18:05
S64	4	"107592".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 18:09

S65	6	((("5869387") or ("5891764") or ("5985681") or ("6221738") or ("6335541") or ("6365933")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/08/06 18:10
S66	6	((("5869387") or ("5891764") or ("5985681") or ("6221738") or ("6335541") or ("6365933")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/08/06 19:59
S67	3	("6489209").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 20:59
S68	28	(US-6489189-\$ or US-6221738-\$ or US-6475840-\$ or US-6479333-\$ or US-6331457-\$ or US-6444390-\$ or US-6432684-\$ or US-6160279-\$ or US-6048758-\$ or US-5932893-\$ or US-5693541-\$ or US-6482684-\$ or US-5891764-\$ or US-5985681-\$ or US-6335541-\$ or US-6365933-\$ or US-5869387-\$).did. or (US-20020043662-\$ or US-20020038889-\$ or US-20020014625-\$ or US-20020008286-\$ or US-20010034088-\$).did. or (JP-2001035787-\$ or JP-2001060551-\$ or JP-08078329-\$).did. or (JP-2001035787-\$ or JP-2001060551-\$ or JP-08078329-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/08/11 11:34
S69	2	"6107639".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/13 18:39
S70	3	"400144".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 07:58
S71	4	"396512".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 08:05
S72	6	"410153".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 08:08

S73	3	"447114".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 08:10
S74	4	"446374".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 08:12
S75	798	(micro-mirror micro adj mirror) and mems	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 08:13
S76	332	(micro-mirror micro adj mirror) and mems.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 08:13
S77	105	(micro-mirror micro adj mirror) and mems.ti,ab,clm.	USPAT	OR	ON	2004/10/14 08:57
S78	4	"336374".ap.	USPAT	OR	ON	2004/10/14 08:58
S79	5	"336374".ap.	US-PGPUB; USPAT	OR	ON	2004/10/14 08:58
S80	3	"446374".ap.	US-PGPUB; USPAT	OR	ON	2004/10/14 08:59
S81	4	"454523".ap.	US-PGPUB; USPAT	OR	ON	2004/10/14 08:59
S82	4	"454423".ap.	US-PGPUB; USPAT	OR	ON	2004/10/14 09:03
S83	4	"454304".ap.	US-PGPUB; USPAT	OR	ON	2004/10/14 09:53
S84	4	"644633".ap.	US-PGPUB; USPAT	OR	ON	2004/10/14 09:59
S85	4	((("20040155278") or ("20030227035")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 10:09
S86	179	mim adj capacitor.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 10:09

S87	5	mim adj capacitor.ti. and "361"/\$9.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 10:14
S88	0	252/62.3.ccls. and organic adj semiconductor.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 10:17
S89	70	organic adj semiconductor adj material.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 10:17
S90	2	organic adj semiconductor adj material.ti.	USPAT	OR	OFF	2004/10/14 10:17
S91	566	active adj (region film layer) near4 (thickness surface adj roughness P-V rms root-mean-square root adj mean adj square) and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/16 14:46
S92	25	active adj (region film layer) near4 thickness and (surface adj roughness P-V rms root-mean-square root adj mean adj square) and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/16 14:51
S93	7	active adj (region film layer) near4 (surface adj roughness P-V rms root-mean-square root adj mean adj square) and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/16 14:52
S94	7	active adj (region film layer) near4 (surface adj roughness P-V rms root-mean-square root adj mean adj square) and (thin adj film adj transistor tft).ti,ab,clm. and surface adj roughness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/16 15:57
S95	0	wo-0104939\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/16 15:57
S96	1	wo-200104939\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/16 15:58

S97	2	"6628326".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/16 16:15
S98	4	"107592".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/16 16:15
S99	1	"20010003659".pn. and upper	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:07
S10 0	0	upper adj2 surface near4 active adj region near4 mobility and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:08
S10 1	11	channel near4 active adj region near4 mobility and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:11
S10 2	24	channel near4 thickness near4 thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:15
S10 3	0	"channel (" \$3 near4 thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:15
S10 4	0	"channel region (" \$3 near4 thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:19
S10 5	59	channel adj depth and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 10:22
S10 6	59	channel adj depth and thin adj film adj transistor and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 11:12

S10 7	4	"187414".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/17 11:12
S10 8	2320	(257/347).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:20
S10 9	281	((257/347).CCLS.) and thin adj film adj transistor.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:23
S11 0	7133	((257/49) or (257/52) or (257/59) or (257/63) or (257/66) or (257/70) or (257/75) or (257/76) or (257/347) or (438/96) or (438/149)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:37
S11 1	5	(((257/49) or (257/52) or (257/59) or (257/63) or (257/66) or (257/70) or (257/75) or (257/76) or (257/347) or (438/96) or (438/149)).CCLS.) and (surface adj2 roughness P-V peak near1 valley) near8 active and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:37
S11 2	7253	((257/49) or (257/52) or (257/59) or (257/63) or (257/66) or (257/70) or (257/75) or (257/76) or (257/347) or (438/166) or (438/149)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:37
S11 3	7	(((257/49) or (257/52) or (257/59) or (257/63) or (257/66) or (257/70) or (257/75) or (257/76) or (257/347) or (438/166) or (438/149)).CCLS.) and (surface adj2 roughness P-V peak near1 valley) near8 active and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 12:54
S11 4	2	jp-2001023899\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 13:13

S11 5	0	energy adj research adj laborator\$3.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 13:14
S11 6	2969	semiconductor adj energy adj laborator\$3.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 13:14
S11 7	13	semiconductor adj energy adj laborator\$3.as. and (P-V peak near2 valley roughness).clm. and (thin adj film adj transistor tft otft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 13:15
S11 9	2	(("6,764,928") or ("6,093,587")). PN.	US-PGPUB; USPAT	OR	OFF	2005/05/09 10:46
S12 0	2	(("6,107,693") or ("6,093,587")). PN.	US-PGPUB; USPAT	OR	OFF	2005/05/09 10:46
S12 1	2	(("6,107,639") or ("6,093,587")). PN.	US-PGPUB; USPAT	OR	OFF	2005/05/09 10:47
S12 2	1	("20010003659").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/09 11:58
S12 3	2	(heat adj treat\$4 anneal\$3) near4 (p-v peak adj2 valley) and (germanium near3 silicon SiGe GeSi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 11:59
S12 4	2	("6107639").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/11 16:19

S12 5	139	(US-20010000755-\$ or US-20010003659-\$ or US-20010015440-\$ or US-20010025958-\$ or US-20010032986-\$ or US-20010034088-\$ or US-20010046729-\$ or US-20020008286-\$ or US-20020013114-\$ or US-20020014625-\$ or US-20020027247-\$ or US-20020038889-\$ or US-20020039831-\$ or US-20020043660-\$ or US-20020043662-\$ or US-20020066931-\$ or US-20020100909-\$ or US-20020102823-\$ or US-20020113241-\$ or US-20020113248-\$ or US-20020119585-\$ or US-20020142567-\$ or US-20020164842-\$ or US-20020182785-\$ or US-20020187594-\$ or US-20030015703-\$).did. or (US-20030025118-\$ or US-20030032221-\$ or US-20030038321-\$ or US-20030042486-\$ or US-20030049892-\$ or US-20030054593-\$ or US-20030059986-\$ or US-20030062522-\$ or US-20030062546-\$ or US-20030064571-\$ or US-20030067005-\$ or US-20030089909-\$ or US-20030094658-\$ or US-20030122125-\$ or US-20030160239-\$ or US-20030201443-\$ or US-20040115906-\$ or US-20040144983-\$ or US-20040178726-\$).did. or (US-4597160-\$ or US-4960719-\$ or US-5221365-\$ or US-5243202-\$ or US-5266824-\$ or US-5621224-\$ or US-5643826-\$ or US-5668379-\$ or US-5693541-\$ or US-5693959-\$ or US-5707744-\$ or US-5712496-\$ or US-5714407-\$ or US-5757030-\$ or US-5828080-\$ or US-5849612-\$ or US-5869387-\$ or US-5891764-\$ or US-5893949-\$ or US-5923962-\$ or US-5932893-\$ or US-5943560-\$ or US-5981974-\$ or US-5985681-\$ or US-6011275-\$ or US-6048758-\$).did. or (US-6002597-\$ or US-6002027-\$	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/12 07:45
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S12 6	0	("aya.in.and1").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 07:45
S12 7	2	S125 and aya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 07:46
S12 8	42	S125 and yamazaki.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 07:47
S12 9	1	S125 and yamazaki.in. and "6107639".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 08:06
S13 0	83	?0 adj nm near6 (thick thickness) and "Si.sub."\$5"Ge.sub."\$5 and (P-v peak-to-valley roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 08:57
S13 1	43	S130 and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 08:27
S13 2	17	S131 not (semiconductor adj energy).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 08:56
S13 3	3	("6716726").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 08:30
S13 4	0	S132	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 08:56
S13 5	49	(thick thickness) near4 "Si.sub. "\$5"Ge.sub."\$5 and (P-v peak-to-valley roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:19

S13 6	2	(thick thickness) near4 "Si.sub." "\$4"Ge.sub."\$4 and (P-v peak-to-valley roughness) and active near6 "Si.sub."\$4"Ge.sub." "\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 09:17
S13 7	2	("6350993").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/12 09:17
S13 8	39	("6350993").URPN.	USPAT	OR	OFF	2005/05/12 09:40
S13 9	49	(thick thickness) near4 "Si.sub." "\$5"Ge.sub."\$5 and (P-v peak-to-valley roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:21
S14 0	0	"Si.sub."\$3"Ge.sub."\$3 near4 (active channel) near10 (p-v peak-to-valley surface adj roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:04
S14 1	69	"Si.sub."\$3"Ge.sub."\$3 near4 (active channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:04
S14 2	12	(thick thickness) near4 "Si.sub."\$5 adj "Ge.sub."\$5 and (P-v peak-to-valley roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:20
S14 3	0	(thick thickness) near4 "Si.sub."\$5 adj "Ge.sub."\$5 and (P-v peak-to-valley roughness) and (active adj layer channel) near6 "Si.sub."\$5 adj "Ge.sub."\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:23
S14 4	25	(thick thickness) near4 ("Si.sub." "\$5 adj "Ge.sub."\$5 "Si.sub." "\$5"Ge.sub."\$5) and (P-v peak-to-valley roughness) and (active adj layer channel) near6 ("Si.sub."\$5 adj "Ge.sub."\$5 "Si. sub."\$5"Ge.sub."\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:35
S14 5	7	("Si.sub."\$5 adj "Ge.sub."\$5 "Si. sub."\$5"Ge.sub."\$5) and (P-v peak-to-valley surface adj roughness rmax "r.sub.max") and (active adj layer channel) near6 ("Si.sub."\$5 adj "Ge.sub."\$5 "Si. sub."\$5"Ge.sub."\$5) and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:38

S14 6	0	("Si.sub."\$5 adj "Ge.sub."\$5 "Si. sub."\$5"Ge.sub."\$5) and (P-v peak-to-valley) and (active adj layer channel) near6 ("Si.sub."\$5 adj "Ge.sub."\$5 "Si.sub."\$5"Ge. sub."\$5) and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:39
S14 7	3	("Si.sub."\$5 adj "Ge.sub."\$5 "Si. sub."\$5"Ge.sub."\$5) and (P-v peak-to-valley) and (active adj layer channel) near6 ("Si.sub."\$5 adj "Ge.sub."\$5 "Si.sub."\$5"Ge. sub."\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:20
S14 8	4	"187414".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:35
S14 9	6	orientation adj ratio near6 lattice adj plane	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:29
S15 0	6	orientation adj ratio near6 lattice adj plane and orientation adj ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:33
S15 1	1596	orientation adj ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:33
S15 2	128	orientation adj ratio and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:34
S15 3	53	S152 not semiconductor adj energy adj laboratory.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 13:25
S15 4	2	jp-07321339\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 15:17

S15 5	3	roughness near4 (channel active adj layer) and roughness near4 ("Si.sub."\$5"Ge.sub."\$5 "Si.sub."\$5 near1 "Ge.sub."\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 15:21
S15 6	2	roughness near4 (channel active adj layer) and roughness near4 ("Si.sub."\$5"Ge.sub."\$5 "Si.sub."\$5 near1 "Ge.sub."\$5) and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 15:22
S15 7	3	((("6,764,928") or ("6,093,587")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 07:31
S15 8	2	S157 and (roughness p-v peak-to-valley peak-valley)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 11:27
S15 9	1	S157 and (roughness p-v peak-to-valley peak-valley) and (germanium Ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 07:44
S16 0	2	("6093587").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 07:35
S16 1	0	S157 and (roughness p-v peak-to-valley peak-valley) and (germanium Ge) and "Si.sub."\$5"Ge.sub."\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 07:45
S16 2	1	S157 and (roughness p-v peak-to-valley peak-valley) and (germanium Ge) and "Si"\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 07:46
S16 3	9	sige near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 11:39
S16 4	49	("Si.sub."\$5 near1 "Ge.sub."\$5 "Si.sub."\$5"Ge.sub."\$5 sige) near4 (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 11:42

S16 5	39	("Si.sub."\$5 near1 "Ge.sub."\$5 "Si.sub."\$5"Ge.sub."\$5 sige) near4 (tft thin adj film adj transistor) and (mobility mobilities)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
S16 6	7056	("{101}" "{101}") and (active adj layer channel) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:59
S16 7	312	("{101}" "{101}") near6 ("{111}" "{111}") and (active adj layer channel) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:00
S16 8	53	("{101}" "{101}") near6 ("{111}" "{111}") and (active adj layer channel) and (tft thin adj film adj transistor) and semiconductor adj energy.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:01
S16 9	0	("{101}" "{101}") near6 ("{111}" "{111}") near6 orientation adj ratio and (active adj layer channel) and (tft thin adj film adj transistor) and semiconductor adj energy.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:01
S17 0	11	("{101}" "{101}") near6 ("{111}" "{111}") near6 orientation and (active adj layer channel) and (tft thin adj film adj transistor) and semiconductor adj energy.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:05
S17 1	4	"187414".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:02
S17 2	1	(US-20030032221-\$).did.	US-PGPUB	OR	OFF	2005/05/13 16:04
S17 3	11	("{101}" "{101}") near6 ("{111}" "{111}") near6 (oriented orientation) and (active adj layer channel) and (tft thin adj film adj transistor) and semiconductor adj energy.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S17 4	31	("{101}" "{101}") near6 ("{111}" "{111}") near6 (oriented orientation) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:15

S17 5	155	("[101]" "{101}" "(101)" "(011)" "110") near6 ("[111]" "{111}" "(111)") near6 (oriented orientation) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:16
S17 6	17	("[101]" "{101}" "(101)" "(011)" "110") near6 ("[111]" "{111}" "(111)") near6 (oriented orientation) near3 ratio and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:36
S17 7	1	("[101]" "{101}" "(101)" "(011)" "110") near6 ("[111]" "{111}" "(111)") near6 (oriented orientation) near3 ratio.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:56
S17 8	6632	((257/49) or (257/52) or (257/59) or (257/63) or (257/66) or (257/70) or (257/75) or (257/76) or (257/347) or (438/149) or (438/166)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/05/13 16:57
S17 9	4	S178 and ("{111}" "[111]" near10 ("[101]" "{101}") and thin adj film and silicon and germanium and (roughness p-v peak-to-valley)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 16:58
S18 0	2	"Si.sub.0.99"\$1"Ge.sub.0.01"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:48
S18 1	14	"Si.sub.0.9"\$2"Ge.sub.0.0"\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:45
S18 2	10	"Si.sub.0.9"\$2"Ge.sub.0.0"\$2 and (active channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:45
S18 3	58220	"Si.sub.0.9"\$2"Ge.sub.0.0"\$2 and (active channel) and tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:45
S18 4	0	"Si.sub.0.9"\$2"Ge.sub.0.0"\$2 and (active channel) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:45

S18 5	1	"Si.sub.0.9"\$2"Ge.sub.0.0"\$2 near20 (active channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:46
S18 6	0	"Si.sub.0.9"\$2"Ge.sub.0.0"\$2 near20 (active channel) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:47
S18 7	0	"Si.sub.0.999"\$1"Ge.sub.0.001"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:48
S18 8	1	"Si.sub.0.99"\$1"Ge.sub.0.00"\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:49
S18 9	280	"Si.sub."\$6"Ge.sub."\$6 and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 14:49
S19 0	13	"Si.sub."\$6"Ge.sub."\$6 near20 (active adj layer channel) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 16:48
S19 1	6	GaAs adj light-emitting adj diode and (substrate near3 sapphire)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 16:57
S19 2	0	GaAs near5 light-emitting adj diode.ti.ab. and (substrate near3 sapphire)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:04
S19 3	0	transparent near3 substrate and (surface adj emitting adj light adj emitting adj diodes)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:05
S19 4	0	(sapphire transparent near3 substrate) and (surface adj emitting adj light adj emitting adj diodes)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:11

S19 5	338309	semiconductor	USPAT	OR	ON	2005/05/14 17:06
S19 6	9685	(sapphire transparent near3 substrate) and (light adj emitting adj diodes)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:11
S19 7	1684	(sapphire transparent near3 substrate).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:11
S19 8	1395	(sapphire transparent near1 substrate).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:12
S19 9	115	(sapphire transparent near1 substrate).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm. and surface near1 emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:12
S20 0	45	(sapphire transparent near1 substrate).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm. and surface near1 emitting and gaas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:13
S20 1	25	(sapphire transparent near1 substrate).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm. and surface near1 emitting and (gaas gallium adj arsenide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:14
S20 2	11	((sapphire transparent near1 substrate) near10 (gaas gallium adj arsenide)).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm. and surface near1 emitting and (gaas gallium adj arsenide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:16
S20 3	31	((sapphire transparent near1 substrate) near10 (gaas gallium adj arsenide)).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm. and (active adj layer channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:21
S20 4	6	((sapphire transparent near1 substrate) near10 (gaas gallium adj arsenide)).ti,ab,clm. and (light adj emitting adj diode).ti,ab,clm. and (active adj layer channel) and (gaas gallium adj arsenide).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:41

S20 5	95	substrate near4 transparent near4 (infrared red) and (light adj emitting light-emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:42
S20 6	10	substrate near4 transparent near4 (infrared red) and (light adj emitting light-emitting) adj diode and surface adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 17:42
S20 7	8	substrate near4 transparent near4 infrared and (light adj emitting light-emitting) adj diode and surface adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 18:23
S20 8	76	(kondo near2 katsufumi).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 18:24
S20 9	17	toshiba.as. and (light adj emitting).ti. and current adj blocking adj (film layer region). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 19:11
S21 0	4	"780534".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/14 20:29